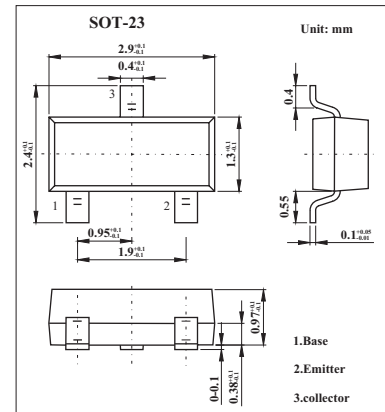


## PNP Silicon Epitaxial Transistor

## 2SB736

## ■ Features

- Micro package.
- Complementary to 2SD780.
- High DC Current Gain:  $h_{FE} = 200$  TYP. ( $V_{CE} = -1.0$  V,  $I_C = -50$  mA)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector to base voltage	$V_{CBO}$	-60	V
Collector to emitter voltage	$V_{CEO}$	-60	V
Emitter to base voltage	$V_{EBO}$	-5.0	V
Collector current (DC)	$I_C$	-300	mA
Total power dissipation	$P_T$	200	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature range	$T_{stg}$	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	$I_{CBO}$	$V_{CB} = -50$ V, $I_E = 0$			-100	nA
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5.0$ V, $I_C = 0$			-100	nA
DC current gain *	$h_{FE}$	$V_{CE} = -1.0$ V, $I_C = -50$ mA	110		400	
Base to emitter voltage *	$V_{BE}$	$V_{CE} = 6.0$ V, $I_C = -10$ mA	-600	-660	-700	mV
Collector saturation voltage *	$V_{CE(sat)}$	$I_C = -300$ mA, $I_B = -30$ mA		-0.35	-0.6	V
Output capacitance	$C_{ob}$	$V_{CB} = -6.0$ V, $I_E = 0$ , $f = 1.0$ MHz		13		pF
Gain bandwidth product	$f_T$	$V_{CE} = -6.0$ V, $I_E = 10$ mA		100		MHz

\* Pulsed:  $PW \leq 350$   $\mu\text{s}$ , duty cycle  $\leq 2\%$

■  $h_{FE}$  Classification

Marking	BW1	BW2	BW3	BW4	BW5
$h_{FE}$	110~180	135~220	170~270	200~320	250~400